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AS1744

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Data Sheet

AS1744, AS1745 High-Speed, Low-Voltage, Dual, Single-Supply, 4Ω, SPDT Analog Switches

1 General Description

The AS1744/AS1745 are high-speed, low-voltage, dual single-pole/double-throw (SPDT) analog switches.

Fast switching speeds, low ON-resistance, and low power-consumption make these devices ideal for single-cell battery powered applications.

These highly-reliable devices operate from a +1.8 to +5.5V supply, are differentiated by inverted logic, and support break-before-make switching.

With low ON-resistance (RON), RON matching, and RON flatness, the devices can accurately switch signals for sample and hold circuits, digital filters, and op-amp gain switching networks.

The devices are available in a 10-pin MSOP package and a 10-pin TDFN package.

10

9

NC1

NC2

COM2

6

COM1

2 Key Features

- ON-Resistance:
 - 4Ω (+5V supply)
 - 5.5Ω (+3V supply)
- Ron Matching: 0.2Ω (+5V supply)
- Ron Flatness: 1Ω (+5V supply)
- Supply Voltage Range: +1.8 to +5.5V
- 1.8V Operation:
 - 9.5Ω ON-Resistance over Temperature
 - 38ns Turn On Time
 - 12ns Turn Off Time
- Current-Handling: 100mA Continuous
- Break-Before-Make Switching
- Rail-to-Rail Signal Handling
- Crosstalk: -90dB at 1MHz
- Off-Isolation: -85dB at 1MHz
- Total Harmonic Distortion: 0.1%
- Operating Temperature Range: -40 to +85°C
- Package Types:
 - 10-pin MSOP
 - 10-pin TDFN

3 Applications

The devices are ideal for use in power routing systems, cordless and mobile phones, MP3 players, CD and DVD players, PDAs, handheld computers, digital cameras, and any other application where high-speed signal switching is required.

Figure 1. Block Diagrams

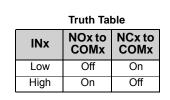
IN

NO1

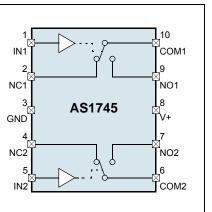
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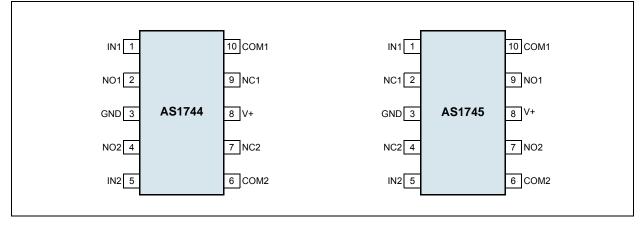
Switches shown for low input.



4 Pinout

Pin Assignments

Figure 2	Pin Assignments	(Top	View)
rigaro z.	1 11 / 10019111101110	(IOP	*1011



Pin Descriptions

Table 1. Pin Descriptions

Pin N	umber	Pin Name	Description	
AS1744	AS1745	r in Name	Description	
10	10	COM1	Analog Switch 1 Common	
6	6	COM2	Analog Switch 2 Common	
3	3	GND	Ground	
1	1	IN1	Analog Switch 1 Logic Control Input	
5	5	IN2	Analog Switch 2 Logic Control Input	
9	2	NC1	Analog Switch 1 Normally Closed Terminal	
7	4	NC2	Analog Switch 2 Normally Closed Terminal	
2	9	NO1	Analog Switch 1 Normally Open Terminal	
4	7	NO2	Analog Switch 2 Normally Open Terminal	
8	8	V+	Input Supply Voltage. +1.8 to +5.5V	

5 Absolute Maximum Ratings

Stresses beyond those listed in Table 2 may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in Section 6 Electrical Characteristics on page 4 is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 2.	Absolute	Maximum	Ratings
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Parameter	Min	Max	Units	Comments
V+, IN1, IN2 to GND	-0.3	+7	V	
COM <i>x</i> , NO <i>x</i> , NC <i>x</i> to GND [†]	-0.3	V+ + 0.3	V	
COM <i>x</i> , NO <i>x</i> , NC <i>x</i> Continuous Current	-100	+100	mA	
COM <i>x</i> , NO <i>x</i> , NC <i>x</i> Peak Current	-150	+150	mA	Pulsed at 1ms, 10% duty cycle
Continuous Power Dissipation (TAMB = +70°C)		330	mW	Derate at 4.7mW/ºC above +70°C
Electro-Static Discharge		1000	V	HBM Mil-Std883E 3015.7 methods
Latch Up Immunity		100	mA	Norm: JEDEC 17
Operating Temperature Range	-40	+85	°C	
Junction Temperature		150	°C	
Storage Temperature Range	-65	+150	°C	
Package Body Temperature		+260	°C	The reflow peak soldering temperature (body temperature) specified is in accordance with IPC/JEDEC J-STD-020C "Moisture/Reflow Sensitivity Classification for Non-Hermetic Solid State Surface Mount Devices"

[†] Signals on pins COM1, COM2, NO1, NO2, NC1, or NC2 that exceed V+ or GND are clamped by internal diodes. Limit forward-diode current to the maximum current rating.

6 Electrical Characteristics

 $V_{+} = +4.5$ to 5.5V, $V_{IH} = +2.4V$, $V_{IL} = +0.8V$, $T_{AMB} = T_{MIN}$ to T_{MAX} (unless otherwise specified). Typ Values @T_{AMB} = +25°C.

Table 3. +5V Supply Electrical Characteristics

Symbol	Parameter	Conditions			Тур	Max	Unit
Analog Sw	vitch						
Vcom <i>x</i> , Vno <i>x</i> , Vnc <i>x</i>	Analog Signal Range			0		V+	V
Ron	ON-Resistance	V+ = 4.5V, ICOMx = 10mA, VNOx or VNCx = 0 to V+	TAMB = +25°C TAMB = TMIN to TMAX		2.5	4 4.5	Ω
	ON-Resistance		TAMB = $+25^{\circ}C$		0.1	0.2	
∆Ron	Match Between Channels ¹	V+ = 4.5 V , ICOM x = 10mA, VNO x or VNC x = 0 to V+	TAMB = TMIN to TMAX		0.1	0.2	Ω
	ON-Resistance		Тамв = +25°С		0.5	1	
RFLAT(ON)	Flatness ²	V+ = 4.5V, ICOMx = 10mA, VNOx or VNCx = 0 to V+	TAMB = TMIN to TMAX		0.0	1.2	Ω
INO <i>x</i> (OFF),	NOx or NCx Off-	V+ = 5.5V, VCOMx = 1 or 4.5V,	Тамв = +25°С	-0.1	±0.01	0.1	nA
INC <i>x</i> (OFF)	Leakage Current ³	V_{NOx} or $V_{NCx} = 4.5$ or $1V$	TAMB = TMIN to TMAX	-0.3		0.3	ПА
	COMx Off-	V+ = 5.5V, VCOMx = 1 or 4.5V,	Тамв = +25°С	-0.1	±0.01	0.1	n۸
ICOM <i>x</i> (OFF)	Leakage Current ³	V_{NOx} or $V_{NCx} = 4.5$ or $1V$	TAMB = TMIN to TMAX	-3		3	nA
	COM <i>x</i> On-	V+ = 5.5V, VCOMx = 4.5 or 1V,	Тамв = +25°С	-0.4	±0.1	0.4	- ^
ICOM <i>x</i> (ON)	Leakage Current ³	V_{NOx} or V_{NCx} = 4.5 or 1V	TAMB = TMIN to TMAX	-4		4	nA
Logic Inpu	it: INx			1			
Vih	Input Logic High			2.4			V
VIL	Input Logic Low				0.8	V	
lih, li∟	Input Leakage Current	VIN <i>x</i> = 0 or +5.5V		-100	5	100	nA
Switch Dy	namic Characteris	tics					
ton	T 0 T 3	VNOx or VNCx = 3V, RLOAD = 300Ω ,	Тамв = +25°С		14	17	ns
ton	Turn On Time ³	CLOAD = 35pF, Figure 12	TAMB = TMIN to TMAX			18	115
tOFF	T 0 (T 3	VNOx or VNCx = 3V, RLOAD = 300Ω ,	Тамв = +25°С		4	6	ns
IOFF	Turn Off Time ³	CLOAD = 35pF, Figure 12	TAMB = TMIN to TMAX			8	115
tввм	Break-Before-	VNOx or VNCx = 3V, RLOAD = 300Ω ,	Тамв = +25°С		10		-
LDDIVI	Make ³	CLOAD = 35pF, Figure 13	TAMB = TMIN to TMAX	1			ns
Q	Charge Injection	VGEN = 2V, RGEN = 0, CLOAD =	1.0nF, Figure 14		7		рС
CNOx(OFF), CNCx(OFF)	NO <i>x</i> , NC <i>x</i> Off- Capacitance	V_{NOx} or $V_{NCx} = GND$, f = 1M	Hz, Figure 15		20		pF
CCOM <i>x</i> (ON)	COM <i>x</i> On- Capacitance	Vсом <i>x</i> = GND, f = 1MHz,	Figure 15		56		pF
	Δ	f = 10MHz, RLOAD = 50Ω, 0 Figure 16		-52			
Viso	Off-Isolation ⁴	f = 1MHz, RLoad = 50Ω, C Figure 16		-85		dB	
)/27	5	f = 10MHz, RLOAD = 50Ω, 0 Figure 16		-52			
Vст	Crosstalk ⁵	f = 1MHz, RLOAD = 50Ω, C Figure 16		-90		dB	
THD	Total Harmonic Distortion	$f = 20$ Hz to 20kHz, VNOx = 5Vp-p, RLOAD = 600 Ω			0.1		%
Power Sup				1	I		L
+	Positive Supply Current	V+ = 5.5V, VINx = 0 or V+			0.01	1.0	μA

 $V_{+} = +2.7$ to 3.6V, $V_{IH} = +2.0V$, $V_{IL} = +0.4V$, $T_{AMB} = T_{MIN}$ to T_{MAX} (unless otherwise specified). Typ values @ $T_{AMB} = +25^{\circ}C$. Table 4. +3V Supply Electrical Characteristics

Analog Switch0V $VOOX, VNCx} VNCx, VNCxAnalog Signal Range0V+RONON-ResistanceV+=2.7V, ICOMx = 10mA, VNOx or VNCx = 0 to V+TAMB = +25°C55\Delta RONON-ResistanceV+ = 2.7V, ICOMx = 10mA, VNOx or VNCx = 0 to V+TAMB = +25°C0.10.2\Delta RONON-ResistanceV+ = 2.7V, ICOMx = 10mA, VNOx or VNCx = 0 to V+TAMB = +25°C1.52RFLAT(ON)ON-ResistanceV+ = 2.7V, ICOMx = 10mA, VNOx or VNCx = 0 to V+TAMB = +25°C1.52INOX(OFF), INOX or NCx Off-Leakage Current 3V+ = 3.3V, VCOMx = 1 or 3V, VNOx or VNCx = 3 or 1VTAMB = +25°C0.10.1ICOMX(OFF)COM x Off-LeakageCurrent 3V+ = 3.3V, VCOMx = 1 or 3V, VNOx or VNCx = 3 or 1VTAMB = +25°C0.10.1ICOMX(OFF)COM x Off-LeakageCurrent 3V+ = 3.3V, VCOMx = 1 or 3V, VNOx or VNCx = 3 or 1VTAMB = +25°C0.10.4ICOMM(ON)COMx On-LeakageCurrent 3V+ = 3.3V, VCOMx = 1 or 3V, VNOx or VNCx = 1 or 3V, VNOx or VNCx = 1 or 3V, VNOx or VNCx = 1 or 3VTAMB = +25°C0.10.4VIIIInput Logic HighVIIIVINX = 0 or +5.5V-1005100Switch Dynamic CharacteristicsVINX or VNCx = 2V, RLOAD = 30002, CLOAD = 35pF, Figure 12TAMB = +25°C1723ToFTurn Off Time 3VNOX or VNCx = 2V, RLOAD = 30002, CLOAD = 35pF, Figure 12TAMB = +25°C110TAMB = TININ to TMAX28TAMB = 100 TMAX28100TAMB = TININ to TMAX28TAMB = 125°C1$	Symbol	Parameter	Conditions			Тур	Max	Unit
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $	Analog Sw	itch						
RonON-ResistanceVNOx or VNCx= 1 to VHC VNOx or VNCx = 1 to VHTAMB = TMIN to TMAX8ΔRonON-Resistance Match Between Channels 1V+ = 2.7V, ICOMx = 10mA, VNOx or VNCx = 0 to V+TAMB = +25°C0.10.2RFLAT(ON)ON-Resistance Flatness 2V+ = 2.7V, ICOMx = 10mA, VNOx or VNCx = 0 to V+TAMB = +25°C1.52INOX(OFF) INCX(OFF)ON-Resistance Flatness 2V+ = 3.3V, VCOMx = 1 or 3V, VNOx or VNCx = 3 or 1VTAMB = +25°C0.1±0.01ICOMX(OFF)COMX ONF-Leakage Current 3V+ = 3.3V, VCOMx = 1 or 3V, VNOx or VNCx = 3 or 1VTAMB = +25°C-0.1±0.010.1ICOMX(OFF)COMX ON-Leakage Current 3V+ = 3.3V, VCOMx = 1 or 3V, VNOx or VNCx = 3 or 1VTAMB = +25°C-0.4±0.10.4ICOMX(ON)COMX ON-Leakage Current 3V+ = 3.3V, VCOMx = 1 or 3V, VNOx or VNCx = 1 or 3V, TAMB = TMIN to TMAX-0.41.0.4LOBINDU: (INX)Input Logic High2.0VHInput Logic Clow1.0.2-0.12.0IH, ILInput Logic Low2.0IH, ILInput Logic Clow1.02.0IUInput Logic Clow1.02.0INTurn On Time 3VNOx or VNCx = 2V, RLOAD = 300Ω, CLOAD = 35pF, Figu	VNO <i>x</i> ,	Analog Signal Range			0		V+	V
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	RON	ON-Resistance		Тамв = +25°С		5	5.5	Ω
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	T CON	ON Resistance	V_{NOx} or $V_{NCx} = 0$ to V_{+}	TAMB = TMIN to TMAX			8	32
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	ΔRon	Match Between				0.1	-	Ω
$ \begin{array}{c c c c c c c c c c c c c c c c c c c $				TAMP - +25°C		15	2	
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	RFLAT(ON)					1.5		Ω
$ \begin{array}{c c} \mbox{COM} \mbox{COFF} \\ \mbox{Current}^{3} & V + = 3.3V, VCOMx = 1 or 3V, VONX or VNCx = 3 or 1V \\ \mbox{VNOx or VNCx} = 3 or 1V \\ \mbox{VNOx or VNCx} = 3 or 1V \\ \mbox{TAMB} = TMIN to TMAX & -3 & 3 \\ \mbox{TAMB} = TMIN to TMAX & -3 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & 4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & -4 & 4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & -4 & -4 & -4 & -4 \\ \mbox{TAMB} = TMIN to TMAX & -4 & -4 & -4 & -4 & -4 & -4 & -4 & -$		NOx or NCx Off-		Тамв = +25°С	-	±0.01	0.1	nA
$\begin{array}{ c c c c c c } \hline COMx(OFF) & Current ^3 & Vixox of Vixox = 3 or 1V & TAMB = TMIN to TMAX & -3 & 3 \\ \hline TAMB = TMIN to TMAX & -3 & 3 \\ \hline TAMB = TMIN to TMAX & -3 & 3 \\ \hline TAMB = TMIN to TMAX & -3 & 3 \\ \hline TAMB = TMIN to TMAX & -4 & 4 \\ \hline \end{tabular}$	- (-)					+0.01		
$\begin{array}{ c c c c c } \hline COMx On-Leakage \\ Current ^{3} & V + = 3.3V, VCOMx = 1 or 3V, \\ VNOx or VNCx = 1 or 3V & TAMB = +25^{\circ}C & -0.4 & \pm 0.1 & 0.4 \\ \hline TAMB = TMIN to TMAX & -4 & -4 & -4 & -4 & -4 & -4 & -4 & -$	ICOM <i>x</i> (OFF)				-	±0.01	-	nA
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$					-	+0.1	-	
Logic Input: (INx)VIHInput Logic High2.00VILInput Logic Low0.40.4IIH,IILInput Leakage CurrentVINx = 0 or ± 5.5 -1005100Switch Dynamic CharacteristicstoNTurn On Time 3VNox or VNcx = 2V, RLOAD = 3000, CLOAD = 35pF, Figure 12TAMB = $\pm 25^{\circ}$ C1723toFFTurn Off Time 3VNox or VNcx = 2V, RLOAD = 3000, CLOAD = 35pF, Figure 12TAMB = $\pm 25^{\circ}$ C68toFFTurn Off Time 3VNox or VNcx = 2V, RLOAD = 3000, CLOAD = 35pF, Figure 12TAMB = $\pm 25^{\circ}$ C1110tBBMBreak-Before-Make 3VNox or VNcx = 2V, RLOAD = 3000, CLOAD = 35pF, Figure 13TAMB = $\pm 25^{\circ}$ C1110QCharge InjectionVGEN = 1.5V, RGEN = 0, CLOAD =TAMB = $\pm 25^{\circ}$ C1120QCharge InjectionVGEN = 1.5V, RGEN = 0, CLOAD =1.0nF, Figure 14020QCharge InjectionVGEN = 1.5V, RGEN = 0, CLOAD =1.0nF, Figure 14020QCharge InjectionVGEN = 1.5V, RGEN = 0, CLOAD =1.0nF, Figure 152020Cooks(OFF), CNCx(OFF)NOx, NCx Off- CapacitanceVCOM x or VNcx = GND, f = 1MHz, Figure 15562020VISOOff-Isolation 4f = 10MHz, RLOAD = 500, CLOAD = 5pF, Figure 16-52523030VISOOff-Isolation 4f = 10MHz, RLOAD = 500, CLOAD = 5pF, Figure 16-523030Torosstalk 5f = 10MHz, RLOAD = 5	ICOM <i>x</i> (ON)					10.1	-	nA
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tonTurn On Time 3NNOX OF VNCX = 2V, RECADE 1TAMB = TMIN to TMAX28 100Ω , CLOAD = 35pF, Figure 12TAMB = TMIN to TMAX28 $10FF$ Turn Off Time 3 $VNOX or VNCx = 2V, RECADE = 300\Omega$, CLOAD = 35pF, Figure 12TAMB = TMIN to TMAX10 $10BM$ Break-Before-Make 3 $VNOX or VNCx = 2V, RECADE = 300\Omega$, CLOAD = 35pF, Figure 13TAMB = TMIN to TMAX10 $10D$ <	Switch Dyr	namic Characteristics						
$\frac{1}{10000000000000000000000000000000000$	ton	3	V_{NOx} or $V_{NCx} = 2V$. $R_{LOAD} = T_{AMB} = +25^{\circ}C$			17	23	-
toFFTurn Off Time 3NNX OF VNXX = 2V, RLOAD = 35pF, Figure 12TAMB = TMIN to TMAX10 $tBBM$ $Break-Before-Make 3$ $VN0x$ or $VNCx = 2V, RLOAD = 35pF, Figure 13$ $TAMB = TMIN to TMAX$ 1110QCharge Injection $VOX OF VNCx = 2V, RLOAD = 35pF, Figure 13$ $TAMB = TMIN to TMAX$ 111QCharge Injection $VGEN = 1.5V, RGEN = 0, CLOAD = 1.0nF, Figure 14$ 00 $CN0x(OFF), CNCx(OFF)$ $NOx, NCx Off-Capacitance$ $VN0x$ or $VNcx = GND, f = 1MHz, Figure 15$ 2010 $CCOMx(ON)$ $COMx On-Capacitance$ $VCOMx = GND, f = 1MHz, Figure 15$ 5610 $VISO$ Off -Isolation 4 $f = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16$ -5211 VCT $Crosstalk^5$ $f = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16$ -85 VCT $Crosstalk^5$ $f = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16$ -90	LON	Turn On Time	300Ω , CLOAD = 35pF, Figure 12	TAMB = TMIN to TMAX			28	ns
$\frac{100}{100}$ $\frac{1000}{100}$ $\frac{100}{100}$	tore	T 011 T 3		Тамв = +25°С		6	8	ne
tBBMBreak-Before-MakeStructureStructureTamb = TMIN to TMAX1QCharge InjectionVGEN = 1.5V, RGEN = 0, CLOAD = 1.0nF, Figure 140CNOx(OFF), CNCx(OFF)NOx, NCx Off- CapacitanceVNOx or VNCx = GND, f = 1MHz, Figure 1520CCOMx(ON)COMx On- CapacitanceVCOMx = GND, f = 1MHz, Figure 1556VISOOff-Isolationf = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16-52VISOOff-Isolationf = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16-85VCTCrosstalkf = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16-52Image: Constalkf = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16-90	torr	Turn Off Time	300 Ω , CLOAD = 35pF, Figure 12	TAMB = TMIN to TMAX			10	ns
QCharge InjectionVGEN = 1.5V, RGEN = 0, CLOAD = 1.0nF, Figure 140 $CNOX(OFF), CNOX(OFF)$ $NOx, NCx Off-Capacitance$ $VNOx or VNCx = GND, f = 1MHz, Figure 15$ 20 $CCOMx(ON)$ $COMx On-Capacitance$ $VcOMx = GND, f = 1MHz, Figure 15$ 56 $VISO$ $Off-Isolation^4$ $f = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16$ -52 VcT $Crosstalk^5$ $f = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16$ -85	t BBM	Drack Defers Make 3		Тамв = +25°С		11		ns
$\frac{CNOX(OFF)}{CNCX(OFF)} = \frac{NOx}{NOx} NCx Off-Capacitance} = VNOx or VNCx = GND, f = 1MHz, Figure 15 = 20$ $\frac{COMx(ON)}{Copacitance} = \frac{COMx}{VCOMx} = GND, f = 1MHz, Figure 15 = 56$ $\frac{CCOMx(ON)}{Capacitance} = \frac{COMx}{F = 10MHz}, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 = -52 = 500$ $\frac{COMx}{F = 10MHz}, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 = -85 = 500$ $\frac{CCOMx}{F = 10MHz}, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 = -52 = 500$ $\frac{CCOMx}{F = 10MHz}, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 = -52 = 500$ $\frac{CCOMx}{F = 10MHz}, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 = -52 = 500$	CDDIM	Break-Belore-Make	300Ω , CLOAD = 35pF, Figure 13	TAMB = TMIN to TMAX	1			110
$ \begin{array}{c c} CNCx(OFF) & Capacitance & VNOx of VNCx = GND, f = 1MH2, Figure 15 & 20 \\ \hline CCOM_{x}(ON) & COM_{x} On-\\ Capacitance & VCOM_{x} = GND, f = 1MHz, Figure 15 & 56 \\ \hline VISO & Off-Isolation ^{4} & f = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 & -52 \\ \hline f = 1MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 & -85 \\ \hline VCT & Crosstalk ^{5} & f = 10MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 & -52 \\ \hline f = 1MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 & -52 \\ \hline f = 1MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 & -52 \\ \hline f = 1MHz, RLOAD = 50\Omega, CLOAD = 5pF, Figure 16 & -90 \\ \hline \end{array} $	Q	Charge Injection	Vgen = 1.5V, Rgen = 0, Cloai	o = 1.0nF, Figure 14		0		рС
$\frac{\text{Comment}(\text{COM})}{\text{Capacitance}} = \frac{\text{Comment}(\text{COM})}{\text{Capacitance}} = \frac{\text{Comment}(\text{COM})}{\text{Capacitance}} = \frac{\text{COM}(\text{COM})}{\text{Capacitance}} = \frac{\text{COM}(\text{COM})}{\text{Capacitance}} = \frac{\text{COM}(\text{COM})}{\text{Capacitance}} = \frac{\text{COM}(\text{COM})}{\text{Capacitance}} = \frac{\text{COM}(\text{CAP})}{\text{Capacitance}} = \frac{\text{COM}(\text{CAP})$		Capacitance	VNOx or $VNCx = GND$, f = 1		20		pF	
VISOOff-Isolation 4 $f = 1$ MHz, RLOAD = 50Ω , CLOAD = 5 pF, Figure 16-85VCTCrosstalk 5 $f = 10$ MHz, RLOAD = 50Ω , CLOAD = 5 pF, Figure 16-52 $f = 1$ MHz, RLOAD = 50Ω , CLOAD = 5 pF, Figure 16-90	CCOM <i>x</i> (ON)	COM <i>x</i> On- Capacitance				56		pF
VCTCrosstalk 5 f = 10MHz, RLOAD = 50 Ω , CLOAD = 5pF, Figure 16-83 $f = 10$ Hz, RLOAD = 50 Ω , CLOAD = 5pF, Figure 16-52 $f = 1$ MHz, RLOAD = 50 Ω , CLOAD = 5pF, Figure 16-90	Viso	Off loolation ⁴	f = 1MHz, RLOAD = 50 Ω , CLOAD = 5pF, Figure 16			-52		dB
VCT Crosstalk ⁵ $f = 1$ MHz, RLOAD = 50 Ω , CLOAD = 5pF, Figure 16 -90	100	OII-Isolation				-85		u.D
	Vст	Crosstell ⁵	f = 10MHz, RLOAD = 50 Ω , CLOAD = 5pF, Figure 16					dB
Power Supply			f = 1MHz, RLOAD = 50Ω, CLOAD = 5pF, Figure 16			-90		
	Power Sup							
I+ Positive Supply Current V+ = 3.6V, VIN = 0 or +3.6V 0.01 1.0	+		V+ = 3.6V, VIN = 0	or +3.6V		0.01	1.0	μA

1. $\Delta Ron = Ron(MAX) - Ron(MIN)$.

2. Flatness is defined as the difference between the maximum and the minimum value of ON-resistance as measured over the specified analog signal ranges.

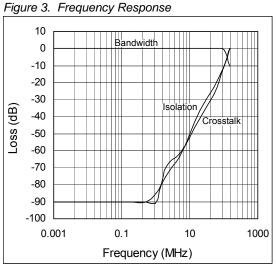
3. Guaranteed by design.

4. Off-Isolation = 20log10(VCOM*x*/VNO*x*), VCOM*x* = output, VNO*x* = input to off switch.

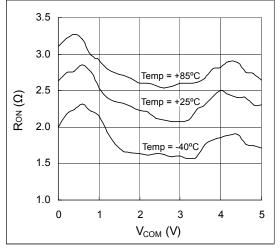
5. Between any two switches.



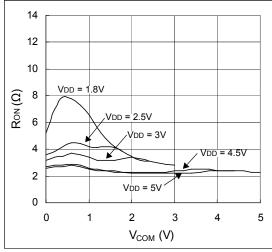
7 Typical Operating Characteristics











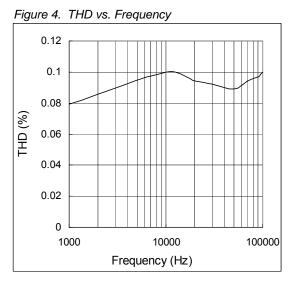
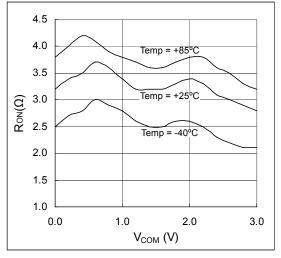
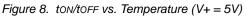


Figure 6. RON vs. VCOM and Temperature (VDD = 3V)





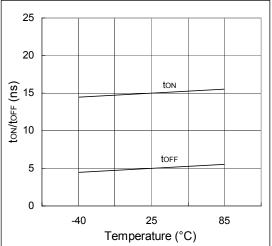


Figure 9. ton/toFF vs. Supply Voltage

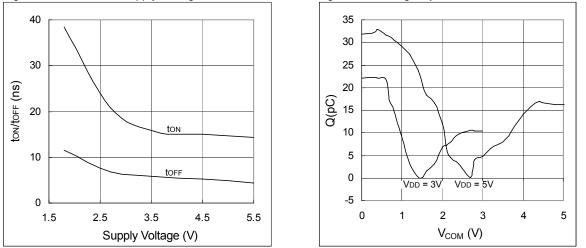


Figure 10. Charge Injection

8 Detailed Description

The AS1744/AS1745 are low ON-resistance, low-voltage, dual analog SPDT switches that operate from a single +1.8 to +5.5V supply.

CMOS process technology allows switching of analog signals that are within the supply voltage range (GND to V+).

ON-Resistance

When powered from a +5V supply, the low Ron (4 Ω max) allows high continuous currents to be switched in a wide range of applications. All devices have low Ron flatness (1 Ω , max) so they can meet or exceed the low-distortion audio requirements of modern portable audio devices.

Bi-Directional Switching

Pins NOx, NCx, and COMx are bi-directional, thus they can be used as inputs or outputs.

Analog Signal Levels

Analog signals ranging over the entire supply voltage (V+ to GND) can be passed with very little change in ON-resistance (see Typical Operating Characteristics on page 6).

Logic Inputs

The AS1744/AS1745 logic inputs (IN*x*) can be driven up to +5.5V regardless of the supply voltage value. For example, with a +3.3V supply, IN+ may be driven low to GND and high to +5.5V. This allows the devices to interface with +5V systems using a supply of less than 5V.

9 Application Information

Power-Supply Sequencing

Proper power-supply sequencing is critical for proper operation. The recommended sequence is as follows:

- 1. V+
- 2. NOx, NCx, COMx

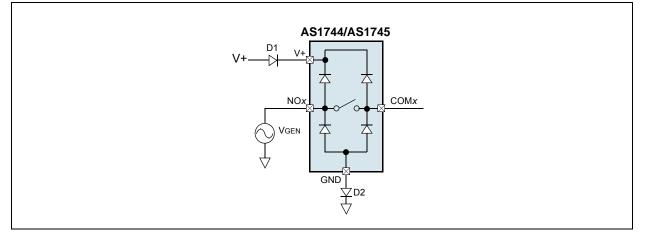
Always apply V+ before applying analog signals, especially if the analog signal is not current-limited. If the above sequence is not possible, and if the analog inputs are not current-limited to less than 30mA, add a small-signal diode as shown in Figure 11 (D1). If the analog signal can dip below GND, add diode D2. Adding these diodes will reduce the analog range to a diode-drop (about 0.7V) below V+ (for D1), and a diode-drop above ground (for D2).

Note: Operation beyond the absolute maximum ratings (see page 3) may permanently damage the devices.

Overvoltage Protection

ON-resistance increases slightly at lower supply voltages.

Figure 11. Overvoltage Protection Using 2 External Blocking Diodes



Adding diode D2 to the circuit shown in Figure 11 causes the logic threshold to be shifted relative to GND. Diodes D1 and D2 also protect against overvoltage conditions.

For example, in the circuit shown in Figure 11, if the supply voltage goes below the absolute maximum rating, and if a fault voltage up to the absolute maximum rating is applied to an analog signal pin, no damage will result.

Note: The supply voltage (V+) must not exceed the absolute maximum rating of +7V.

Power Supply Bypass

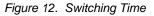
Power supply connections to the devices must maintain a low impedance to ground. This can be done using a bypass capacitor, which will also improve noise margin and prevent switching noise propagation from the V+ supply to other components.

Layout Considerations

High-speed switches require proper layout and design procedures for optimum performance.

- Reduce stray inductance and capacitance by keeping traces short and wide.
- Ensure that bypass capacitors are as close to the device as possible.
- Use large ground planes where possible.

Timing Diagrams and Test Setups



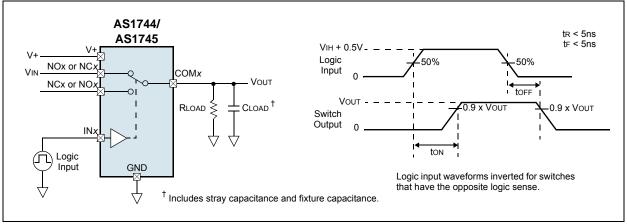
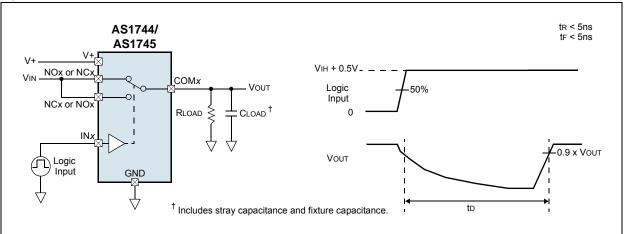


Figure 13. Break-Before-Make Interval





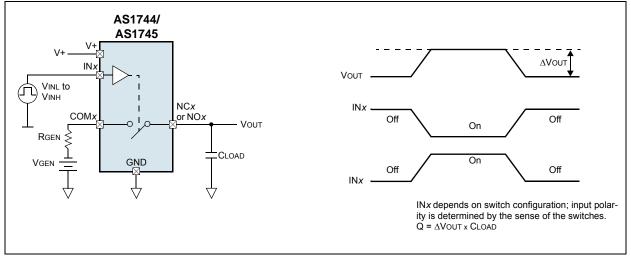


Figure 15. NOx, NCx, and COMx Capacitance

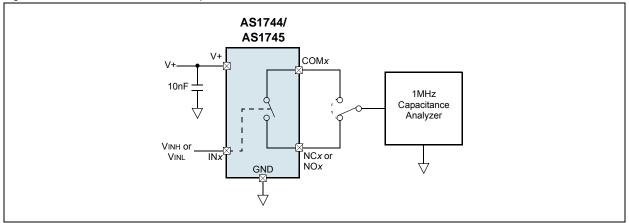
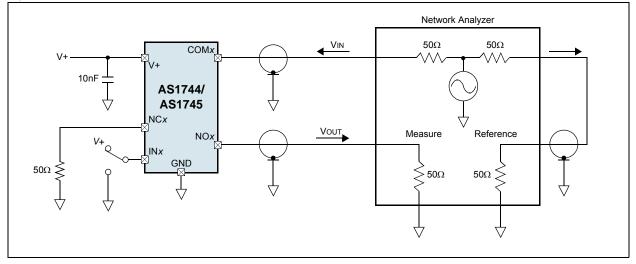


Figure 16. Off-Isolation, On-Loss, and Crosstalk



Notes:

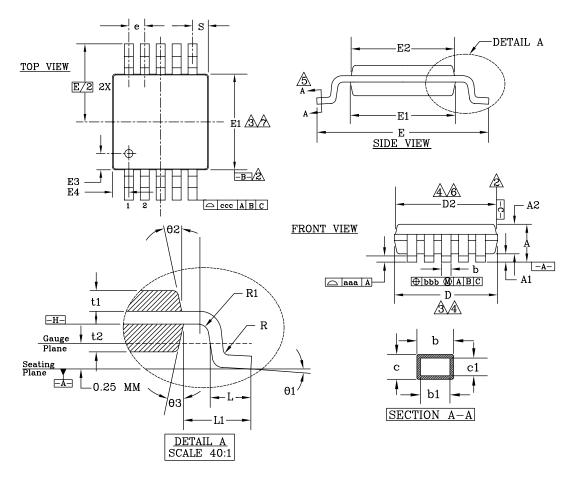
- 1. Measurements are standardized against short-circuit at all terminals.
- Off-isolation is measured between COMx and the off NCx/NOx terminal of each switch. Off-isolation = 20log(Vout/VIN).
- 3. Crosstalk is measured from one channel to all other channels.
- 4. Signal direction through the switch is reversed; worst values are recorded.



Package Drawings and Markings

The devices are available in a 10-pin MSOP package and a 10-pin TDFN package.

Figure 17. 10-pin MSOP Package



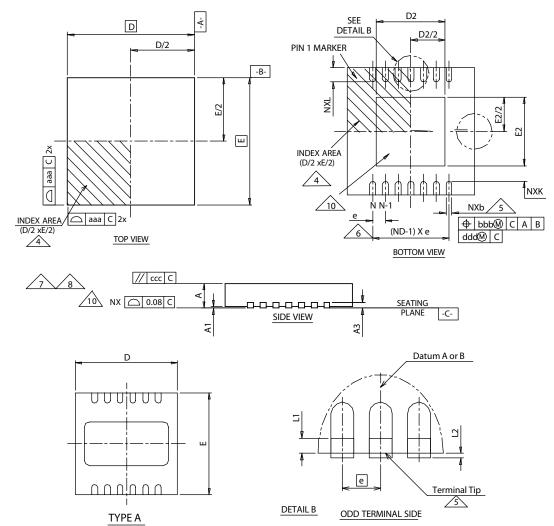
Symbol	Тур	±Tol	Symbol	Тур	±Tol
A	1.10	Max	b	0.23	+0.07/-0.08
A1	0.10	±0.05	b1	0.20	±0.05
A2	0.86	±0.08	С	0.18	±0.08
D	3.00	±0.10	c1	0.15	+0.03/-0.02
D2	2.95	±0.10	θ1	3.0°	±3.0°
E	4.90	±0.15	θ2	12.0°	±3.0°
E1	3.00	±0.10	θ 3	12.0°	±3.0°
E2	2.95	±0.10	L	0.55	±0.15
E3	0.51	±0.13	L1	0.95BSC	-
E4	0.51	±0.13	aaa	0.10	-
R	0.15	+0.15/-0.08	bbb	0.08	-
R1	0.15	+0.15/-0.08	CCC	0.25	-
t1	0.31	±0.08	е	0.50 BSC	-
t2	0.41	±0.08	S	0.50 BSC	-



Notes:

- 1. All dimensions are in millimeters, angles in degrees, unless otherwise specified.
- 2. Datums B and C to be determined at datum plane H.
- 3. Dimensions D and E1 are to be determined at datum plane H.
- 4. Dimensions D2 and E2 are for top package; dimensions D and E1 are for bottom package.
- 5. Cross section A-A to be determined at 0.13 to 0.25mm from lead tip.
- 6. Dimensions D and D2 do not include mold flash, protrusion, or gate burrs.
- 7. Dimensions E1 and E2 do not include interlead flash or protrusion.

Figure 18. 10-pin TDFN Package (3.0x3.0mm)



		_		
Symbol	Min	Тур	Max	Notes
А	0.70	0.75	0.80	1, 2
A1	0.00	0.02	0.05	1, 2
A3		0.20 REF		1, 2
L1			0.15	1, 2
L2			0.13	1, 2
θ	0°		14°	1, 2
K	0.20			1, 2
K2	0.17			1, 2
b	0.18	0.25	0.30	1, 2, 5
е		0.5		
aaa		0.15		1, 2
bbb		0.10		1, 2
CCC		0.10		1, 2
ddd		0.05		1, 2
eee		0.08		1, 2
<u>ggg</u>		0.10		1, 2

Variations					
Symbol	Min	Тур	Max	Notes	
D BSC		3.00		1, 2	
E BSC		3.00		1, 2	
D2	2.20		2.70	1, 2	
E2	1.40		1.75	1, 2	
L	0.30	0.40	0.50	1, 2	
N		10		1, 2	
ND		5		1, 2, 5	

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Notes:

- 1. Dimensioning and tolerancing are compliant with ASME Y14.5M-1994.
- 2. Dimensions are in millimeters, angles in degrees (°).
- 3. N is the total number of terminals.
- 4. The terminal 1 identifier and terminal numbering convention shall conform to *JESD 95-1 SPP-012*. Details of terminal 1 identifier are optional, but must be located within the zone indicated. The terminal 1 identifier may be either a mold, embedded metal or mark feature.
- 5. Dimension b applies to metallized terminal and is measured between 0.15 and 0.30mm from terminal tip.
- 6. ND refers to the maximum number of terminals on D side.
- 7. Variation shown in Figure 18 is for illustration purposes only.
- 8. For variation identifier dimension details, refer to the Dimensions table.
- 9. For a complete set of dimensions for each variation, refer to the Variations table.
- 10. Unilateral coplanarity zone applies to the exposed heat sink slug and the terminals.
- 11. For a rectangular package, the terminal side of the package is determined by:
 - Type 1: Terminals are on the short side of the package.
 - Type 2: Terminals are on the long side of the package.
- 12. Variations specified as NJR (non JEDEC registered), with an additional dash number (e.g., -1, -2) are packages currently not registered with JEDEC.
- 13. When more than one variations exist for the same profile height, body size (DxE), and pitch, then those variations will be denoted by an additional dash number (i.e., -1,-2) for identification. The new variations shall be created based on any or all of the following factors: terminal count, terminal length, and exposed pad sizes.

10 Ordering Information

The devices are available as the standard products shown in Table 5.

Table 5. Ordering Information

Туре	Description	Delivery Form	Package
AS1744G	Dual SPDT Switch	Tube	10-pin MSOP
AS1744G-T	Dual SPDT Switch	Tape and Reel	10-pin MSOP
AS1744V-T [†]	Dual SPDT Switch	Tape and Reel	10-pin TDFN
AS1745G	Dual SPDT Switch	Tube	10-pin MSOP
AS1745G-T	Dual SPDT Switch	Tape and Reel	10-pin MSOP
AS1745V-T [†]	Dual SPDT Switch	Tape and Reel	10-pin TDFN

[†] Available upon request. Contact austriamicrosystems, AG for details.

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Contact Information

Headquarters austriamicrosystems AG A-8141 Schloss Premstaetten, Austria

Tel: +43 (0) 3136 500 0 Fax: +43 (0) 3136 525 01

For Sales Offices, Distributors and Representatives, please visit:

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